

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (U-MOSII)

2SK2986

HIGH CURRENT SWITCHING APPLICATIONS

DC-DC CONVERTER, RELAY DRIVE AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS

Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 4.5 \text{ m}\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 80 \text{ S}$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100 \mu\text{A}$ (Max.) ($V_{DS} = 60 \text{ V}$)
- Enhancement-Mode : $V_{th} = 1.3 \sim 2.5 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage ($R_{GS} = 20 \text{ k}\Omega$)	V_{DGR}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	DC	I_D	55
	Pulse ($t \leq 10 \text{ s}$)	I_{DP}	70
	Pulse ($t \leq 1 \text{ ms}$)		280
Drain Power Dissipation ($T_c = 25^\circ\text{C}$)	P_D	100	W
Single Pulse Avalanche Energy**	E_{AS}	525	mJ
Avalanche Current	I_{AR}	55	A
Repetitive Avalanche Energy*	E_{AR}	10	mJ
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ\text{C}$

THERMAL CHARACTERISTICS

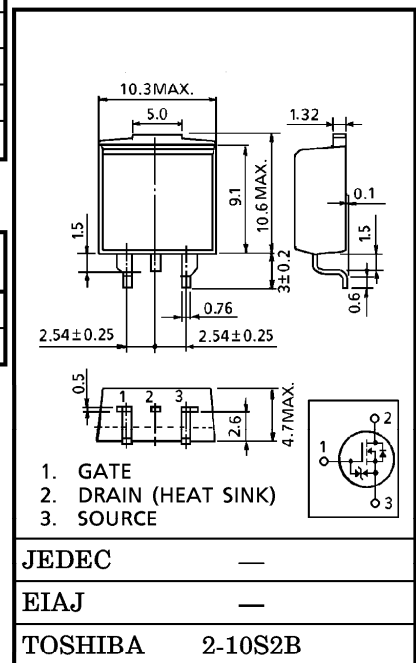
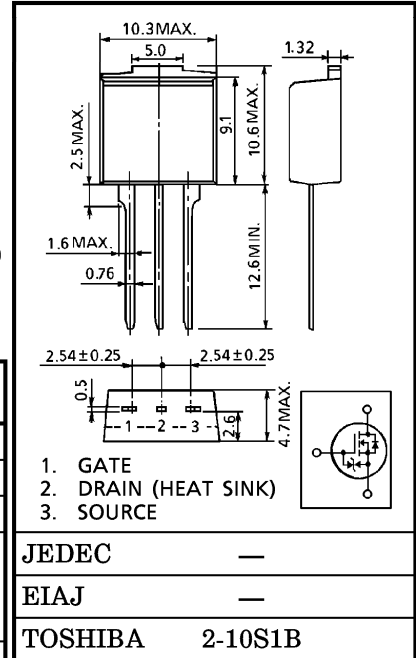
CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel To Case	$R_{th(ch-c)}$	1.25	$^\circ\text{C}/\text{W}$
Thermal Resistance, Channel To Ambient	$R_{th(ch-a)}$	83.3	$^\circ\text{C}/\text{W}$

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = 25 \text{ V}$, $T_{ch} = 25^\circ\text{C}$, $L = 236 \mu\text{H}$, $I_{AR} = 55 \text{ A}$, $R_G = 25 \Omega$

**This transistor is an electrostatic sensitive device.
Please handle with caution.**



Weight : 1.5 g

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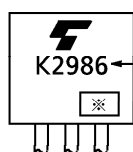
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	—	—	±10	μA	
Drain Cut-off Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	—	—	100	μA	
Drain-Source Breakdown Voltage	V _{(BR) DSS}	I _D = 10 mA, V _{GS} = 0 V	60	—	—	V	
	V _{(BR) DSX}	I _D = 10 mA, V _{GS} = -20 V	40	—	—		
Gate Threshold Voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.3	—	2.5	V	
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 35 A	—	4.5	5.8	mΩ	
		V _{GS} = 4 V, I _D = 35 A	—	5.8	10		
Forward Transfer Admittance	Y _{fs}	V _{DS} = 10 V, I _D = 35 A	40	80	—	S	
Input Capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	—	9300	—	pF	
Reverse Transfer Capacitance	C _{rss}		—	910	—		
Output Capacitance	C _{oss}		—	1435	—		
Switching Time	Rise Time	t _r		—	18	—	ns
	Turn-on Time	t _{on}		—	50	—	
	Fall Time	t _f		—	110	—	
	Turn-off Time	t _{off}		V _{IN} : t _r , t _f < 5 ns Duty ≤ 1%, t _w = 10 μs	—	480	
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q _g	V _{DD} ≐ 48 V, V _{GS} = 10 V, I _D = 55 A	—	210	—	nC	
Gate-Source Charge	Q _{gs}		—	145	—		
Gate-Drain (“Miller”) Charge	Q _{gd}		—	65	—		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I _{DR}	—	—	—	55	A
Pulse Drain Reverse Current	I _{DRP}	t ≤ 10 s	—	—	70	A
		t ≤ 1 ms	—	—	280	
Diode Forward Voltage	V _{DSF}	I _{DR} = 55 A, V _{GS} = 0 V	—	—	-1.5	V
Reverse Recovery Time	t _{rr}	I _{DR} = 55 A, V _{GS} = 0 V	—	60	—	ns
Reverse Recovery Charge	Q _{rr}	dI _{DR} / dt = 50 A / μs	—	50	—	nC

MARKING

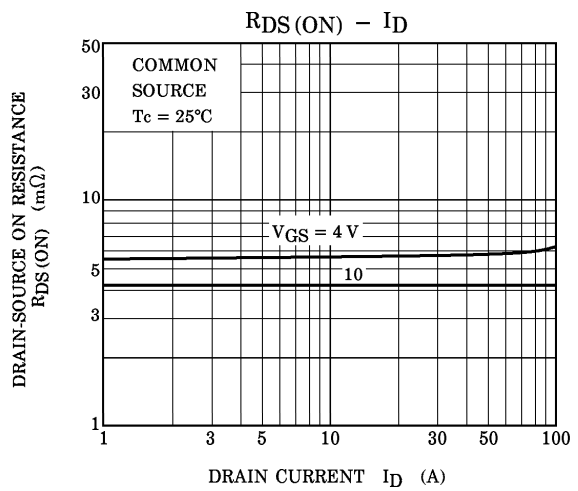
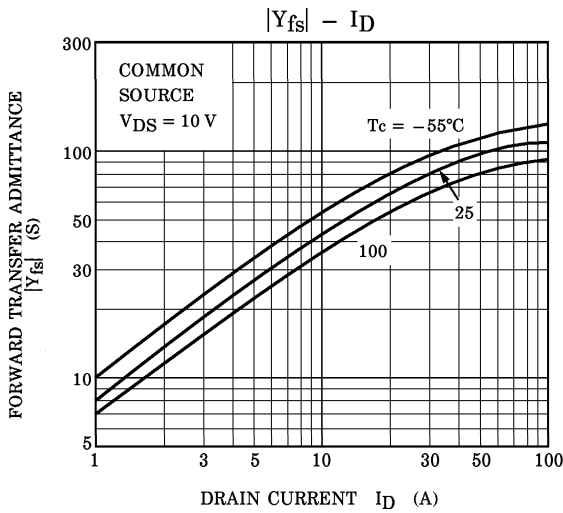
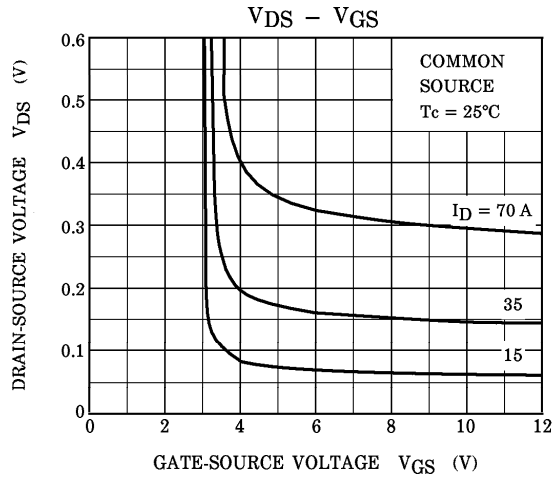
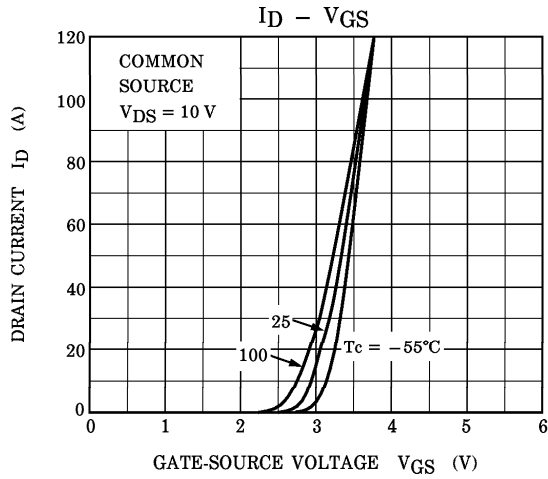
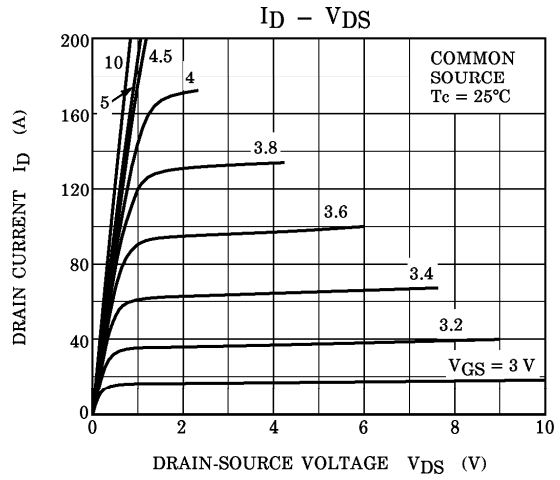
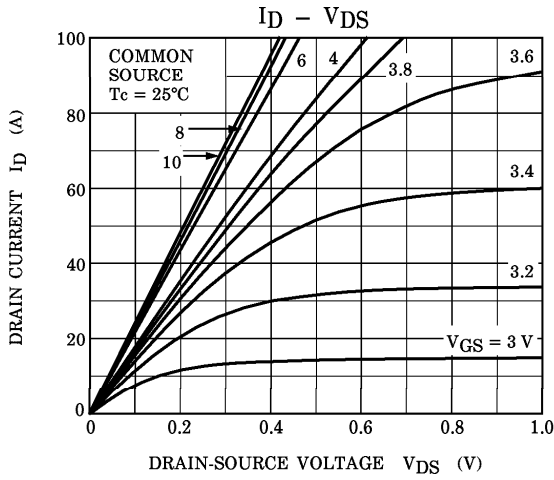


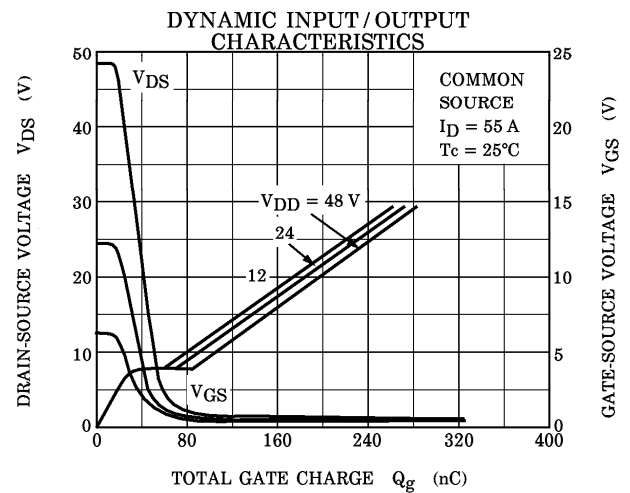
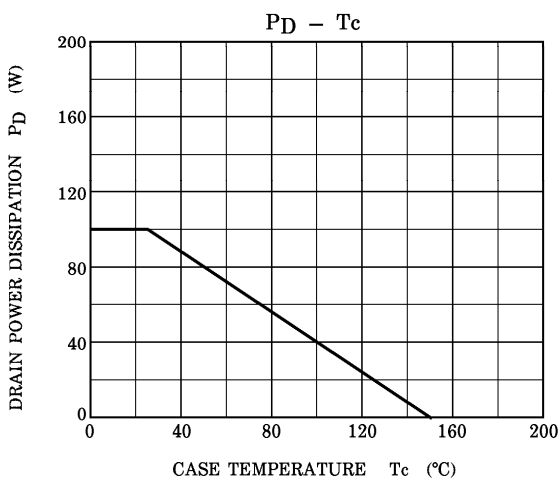
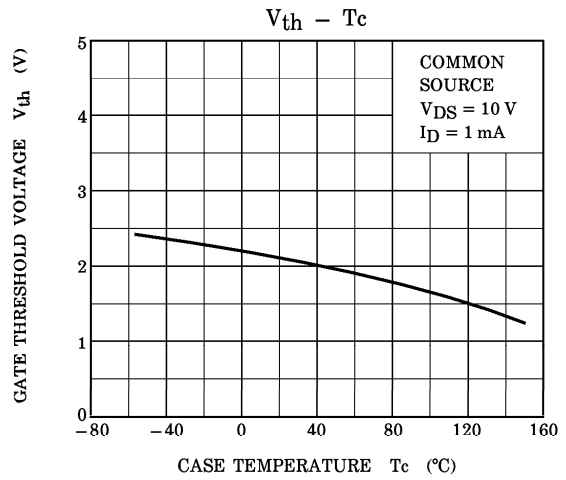
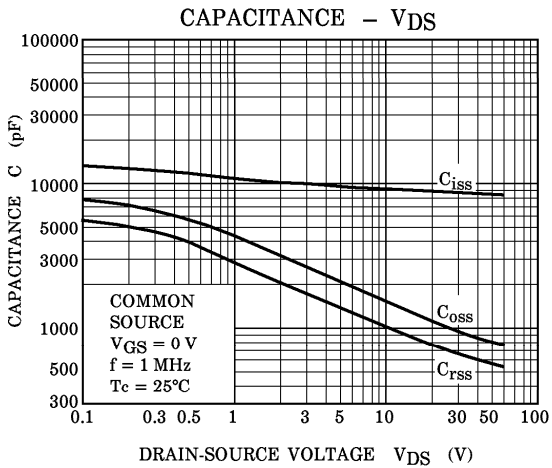
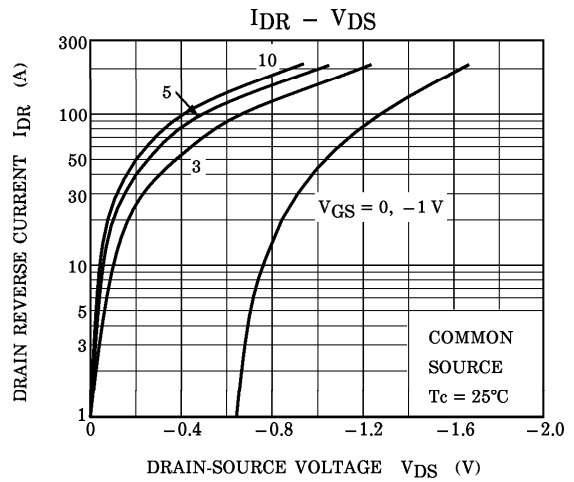
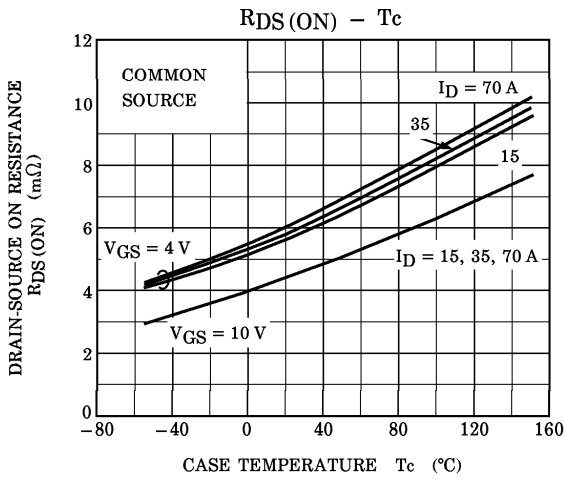
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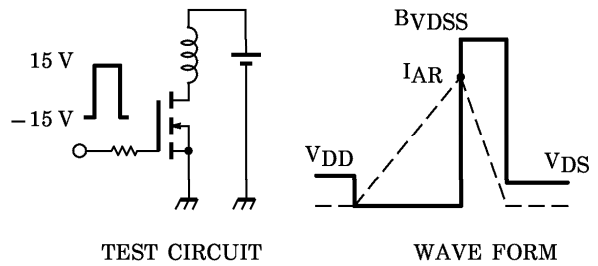
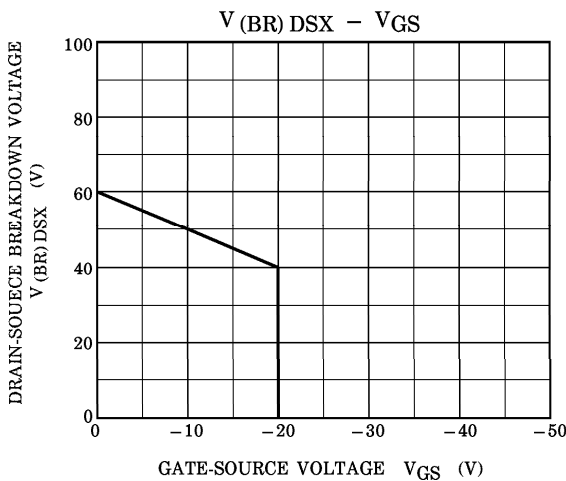
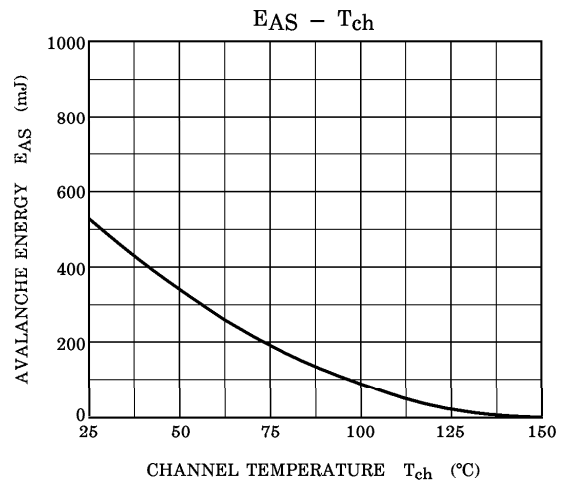
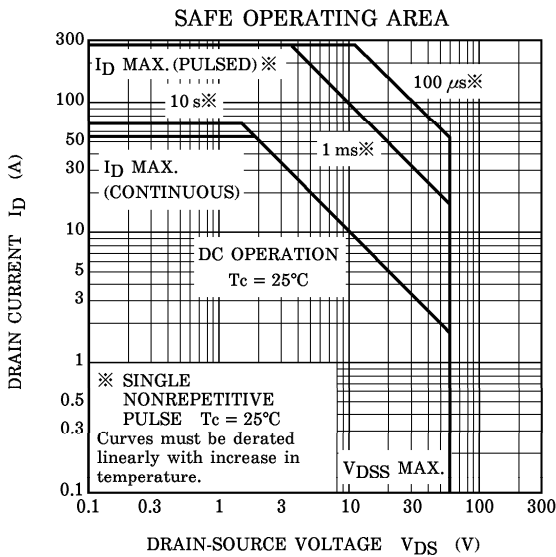
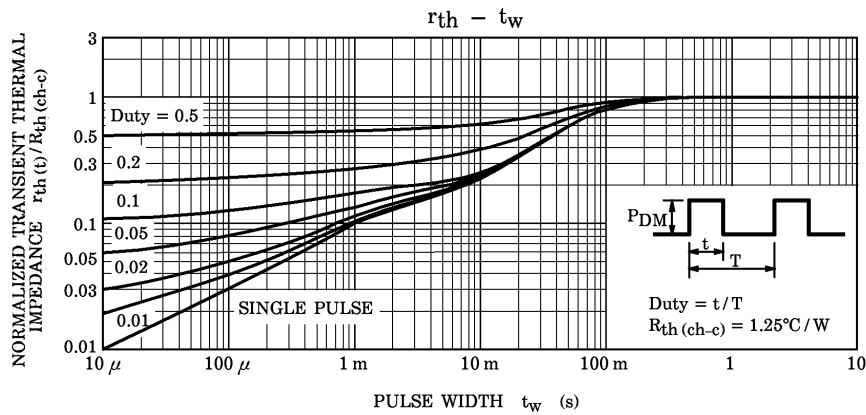
※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







Peak $I_{AR} = 55$ A, $R_G = 25 \Omega$
 $V_{DD} = 25$ V, $L = 236 \mu H$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BV_{DSS}}{BV_{DSS} - V_{DD}} \right)$$